



- ★ Super Low Gate Charge
- ★ Green Device Available
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

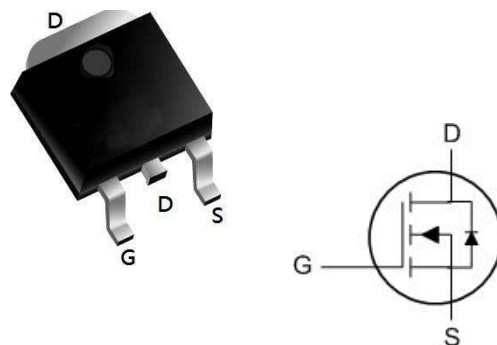
Product Summary

BVDSS	R _{DS(on)}	I _D
100V	95 mΩ	12A

Description

The XXWS12N10 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent R_{DS(on)} and gate charge for most of the synchronous buck converter applications .

The XXWS12N10 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO252 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	100	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	12	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	3.2	A
I _{DM}	Pulsed Drain Current ²	11	A
P _D @T _A =25°C	Total Power Dissipation ³	1	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

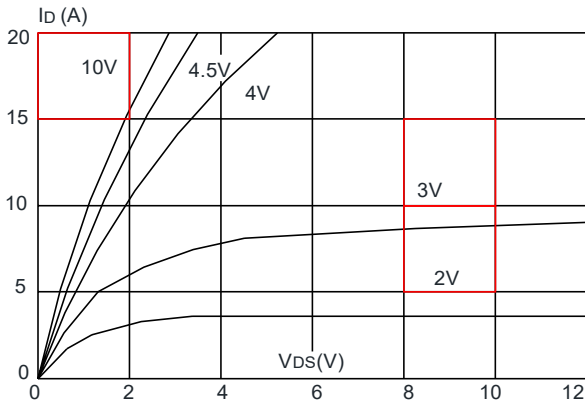
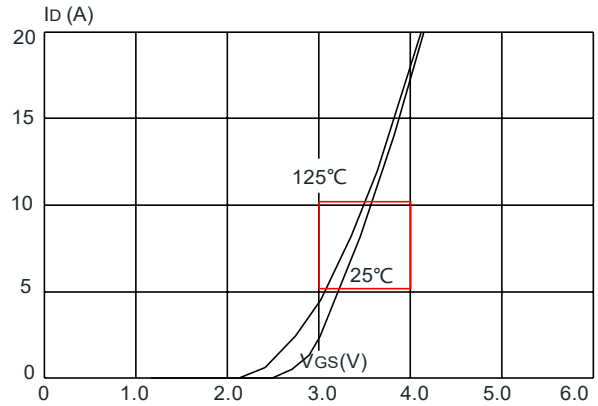
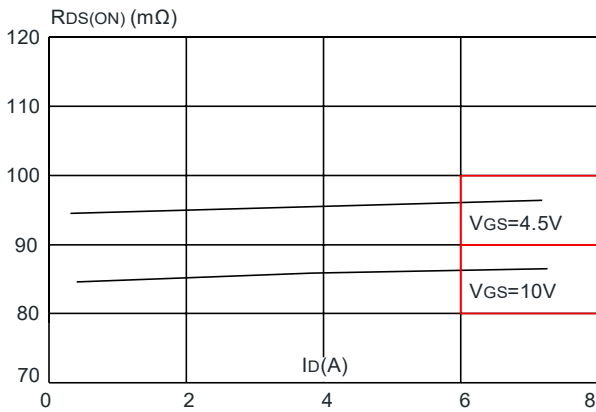
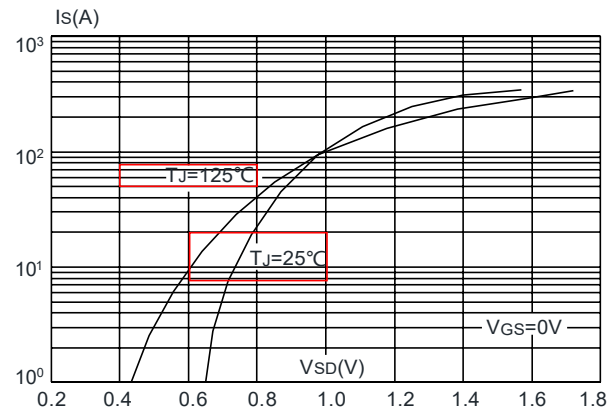
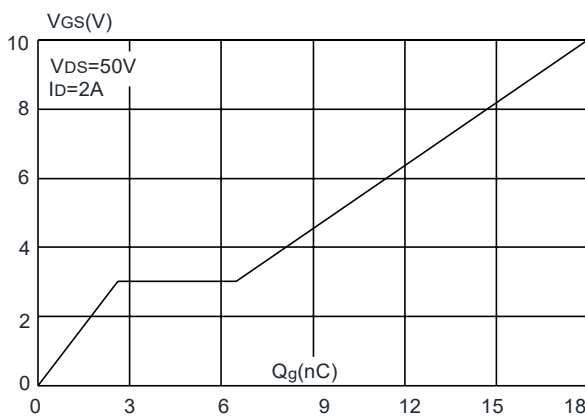
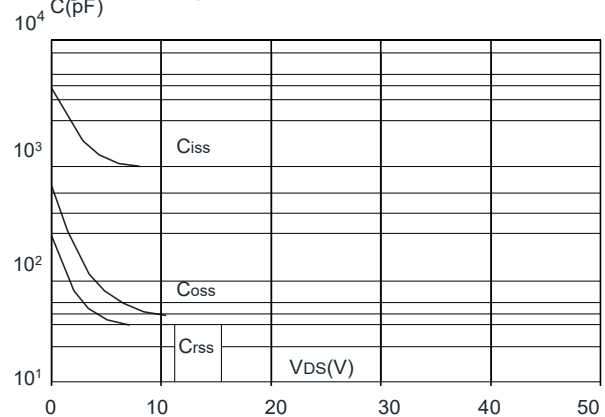
Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹	---	125	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	80	°C/W

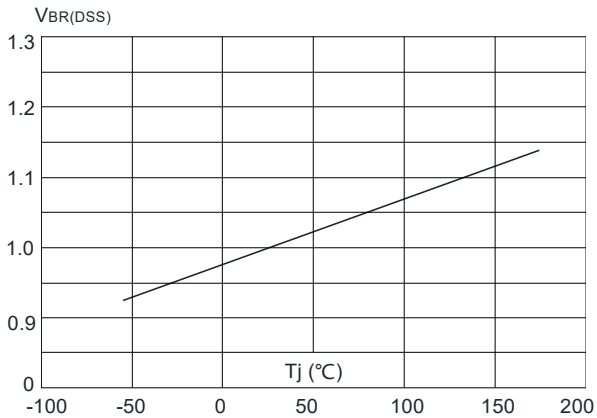
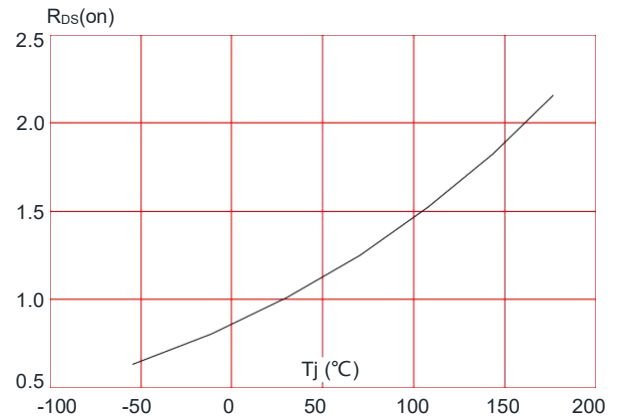
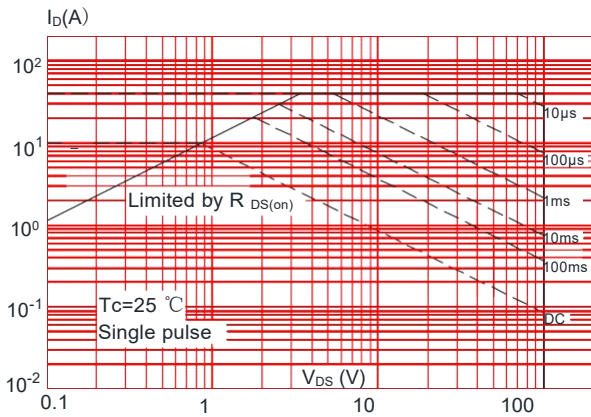
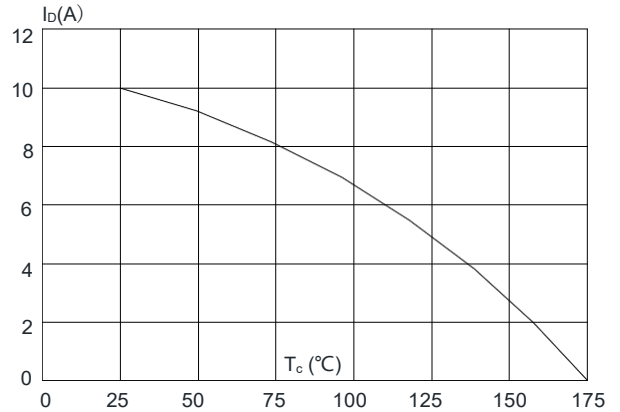
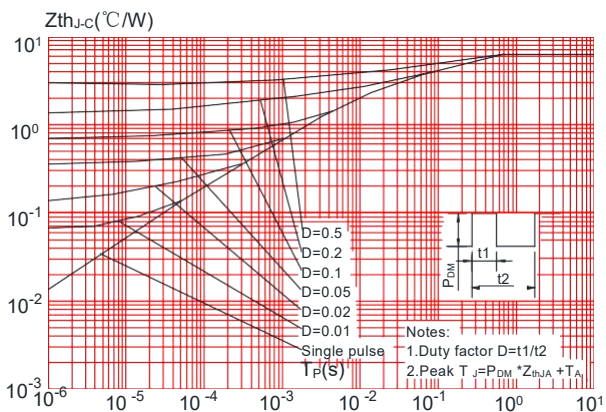
Electrical Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise specified

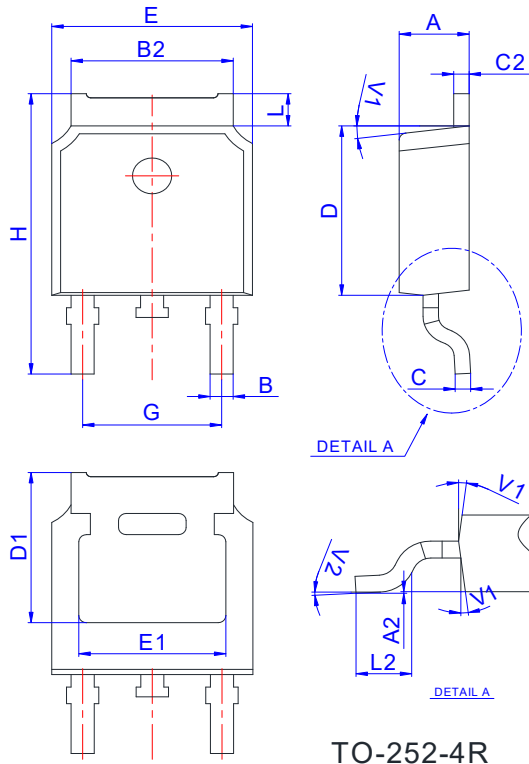
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	100	110	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 100V, V_{GS} = 0V$	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	± 100	nA
On Characteristics ^{note3}						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	1.8	3.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance ^{note2}	$V_{GS} = 10V, I_D = 3A$	-	95	140	m Ω
Dynamic Characteristics ^{note4}						
C_{iss}	Input Capacitance	$V_{DS} = 50V, V_{GS} = 0V,$ $f = 1.0MHz$	-	196	-	pF
C_{oss}	Output Capacitance		-	25.9	-	pF
C_{rss}	Reverse Transfer Capacitance		-	21.4	-	pF
Q_g	Total Gate Charge	$V_{DS} = 50V, I_D = 3A,$ $V_{GS} = 10V$	-	4.3	-	nC
Q_{gs}	Gate-Source Charge		-	3.5	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	3.1	-	nC
Switching Characteristics ^{note4}						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50V, I_{DS}=3A$ $R_G = 2\Omega, V_{GEN} = 10V$	-	14.7	-	ns
t_r	Turn-On Rise Time		-	3.5	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	20.9	-	ns
t_f	Turn-Off Fall Time		-	2.7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current ^{note2}		-	-	4.5	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	12	A
V_{SD}	Drain to Source Diode Forward Voltage ^{note3}	$V_{GS} = 0V, I_S = 3A$	-	-	1.3	V
t_{rr}	Body Diode Reverse Recovery Time	$V_{GS} = 0V, I_F = 3A,$ $di/dt = 100A/\mu s$	-	32.1	-	ns
Q_{rr}	Body Diode Reverse Recovery Time Charge		-	39.4	-	nC
I_{rrm}	Peak Reverse Recovery Current		-	2.1	-	A

Notes:

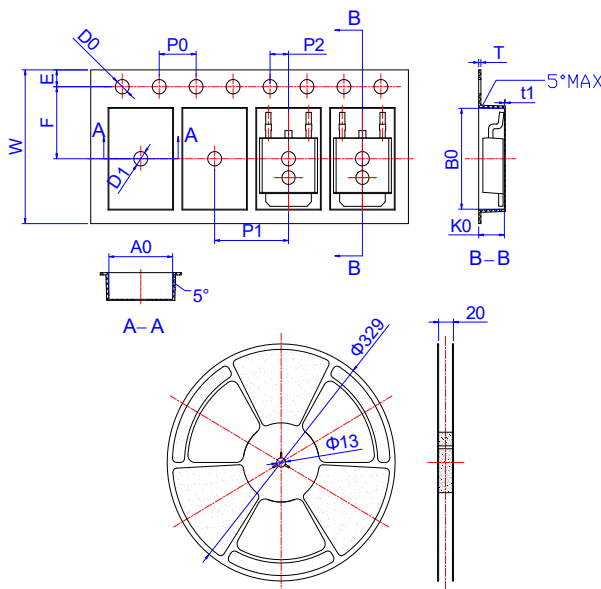
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. $V_{DD}=50$ V, $R_G=50$ Ω , $L=0.3$ mH, starting $T_j=25$ $^{\circ}\text{C}$

Typical Performance Characteristics
Figure 1: Output Characteristics

Figure 2: Typical Transfer Characteristics

Figure 3: On-resistance vs. Drain Current

Figure 4: Body Diode Characteristics

Figure 5: Gate Charge Characteristics

Figure 6: Capacitance Characteristics


N-Ch 100V Fast Switching MOSFETs
Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

Figure 8: Normalized on Resistance vs. Junction Temperature

Figure 9: Maximum Safe Operating Area

Figure 10: Maximum Continuous Drain Current vs. Case Temperature

Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Case


Package Mechanical Data-TO-252-4R


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2		0°	6°		0°	6°

Reel Specification-TO-252-4R


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583